



Absolute Maximum Ratings:

Collector-Emitter Voltage, V_{CE0}	: 50V
Collector-Base Voltage, V_{CB0}	: 75V
Emitter-Base Voltage, V_{EB0}	: 5V
Continuous Collector Current, I_C	: 2A
Base Current, I_B	: 1A
Total Power Dissipation ($T_C = +25^\circ\text{C}$), P_D	: 10W
Derate Above 25°C	: 0.057W/ $^\circ\text{C}$
Operating Junction Temperature, T_J	: -65°C to 200°C
Storage Temperature Range, T_{stg}	: -65°C to 200°C
Thermal Resistance, Junction -to-Case, R_{thJC}	: 17.5°C/W

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ Unless otherwise specified):

Parameter	Symbol	Test Conditions	Min	Max	Unit
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OFF Characteristics

Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 100\text{mA}$, $I_B = 0$ (Note1)	50	-	V
Collector Cutoff Current	I_{CEX}	$V_{CE} = 75\text{V}$, $V_{BE} = 1.5\text{V}$	-	0.1	mA
		$V_{CE} = 45\text{V}$, $V_{BE} = 1.5\text{V}$, $T_C = +150^\circ\text{C}$	-	5	mA
Emitter Cutoff Current	I_{EBO}	$V_{BE} = 5\text{V}$, $I_C = 0$	-	0.1	mA

ON Characteristics (Note 1)

DC Current Gain	h_{FE}	$I_C = 500\text{mA}$, $V_{CE} = 4\text{V}$	40	250	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}$, $I_B = 50\text{mA}$	-	1.2	V
Base-Emitter ON Voltage	$V_{BE(on)}$	$I_C = 500\text{mA}$, $V_{CE} = 4\text{V}$	-	1.4	V

Small-Signal Characteristics

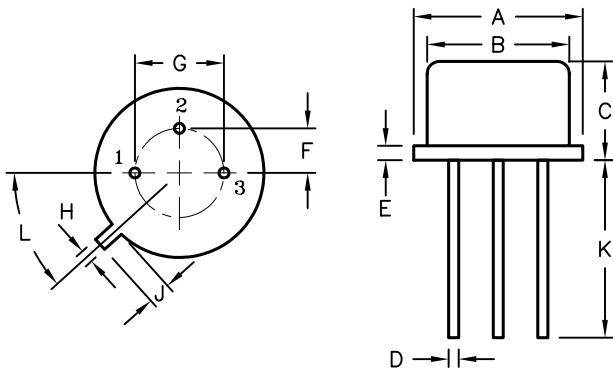
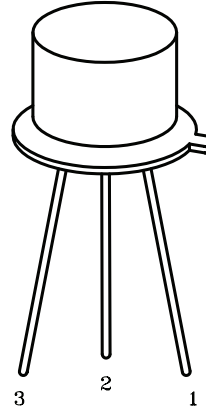
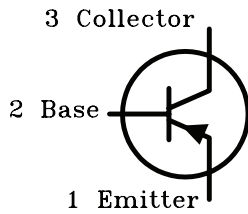
Small-Signal Current Gain	h_{fe}	$I_C = 50\text{mA}$, $V_{CE} = 4\text{V}$, $f = 10\text{MHz}$	5.0	-	-
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Switching Characteristics

Turn-On Time	t_{on}	$V_{CC} = 30\text{V}$, $I_C = 500\text{mA}$, $I_{B1} = 50\text{mA}$	-	100	ns
Turn-Off Time	t_{off}	$V_{CC} = 30\text{V}$, $I_C = 500\text{mA}$, $I_{B2} = 50\text{mA}$	-	1,000	ns

Notes: 1. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.

PNP



Dimensions	A	B	C	D	E	F	G	H	J	K	L
Min.	8.5	7.74	6.09	0.4	-	2.41	4.82	0.71	0.73	12.7	45°
Max.	9.39	8.5	6.6	0.53	0.88	2.66	5.33	0.86	1.02	-	48°

Dimensions : Millimetres

Part Number Table

Description	Part Number
Transistor, Silicon, TO-39, PNP, General Purpose	2N5323

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